Supplementary Materials for "Studies of hot photoluminescence in plasmonically-coupled silicon via variable energy excitation and temperature dependent spectroscopy"

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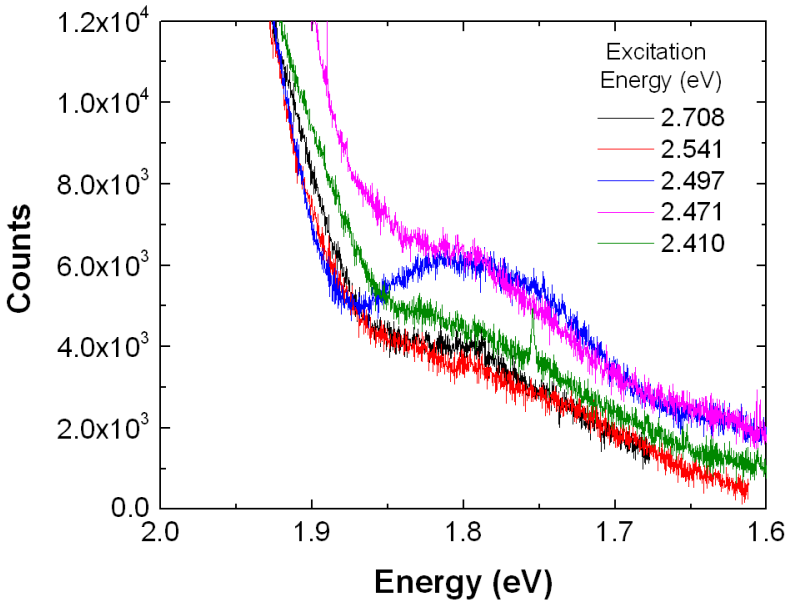

Figure S1. Magnified photoluminescence spectra of d=150 nm plasmonically-coupled silicon nanowire in low energy region demonstrating emission below the silicon bandgap at the L-point.

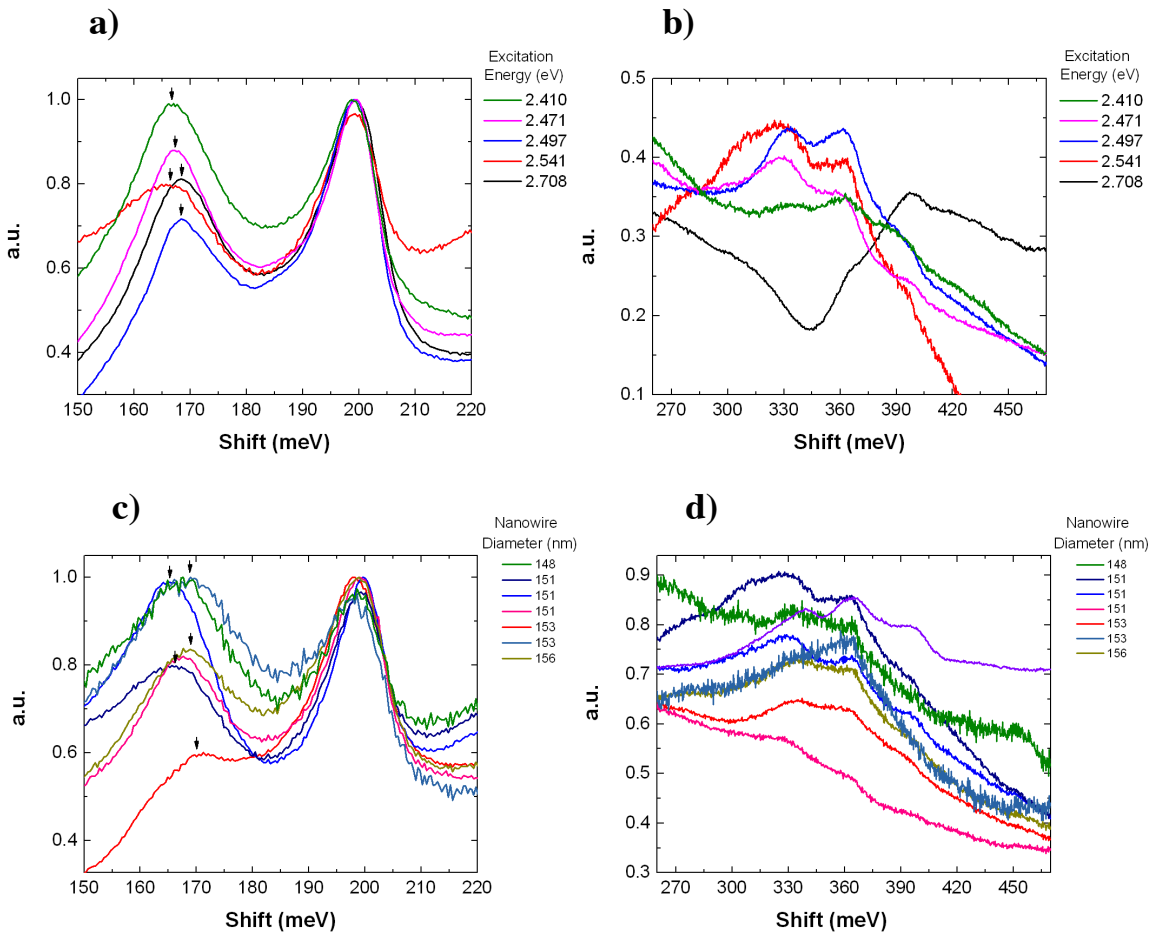

Figure S2. Variation in spectral positions of subpeaks in photoluminescence spectrum of plasmonically-coupled silicon nanowire. (a) variation in band A and (b) band B as a function of excitation energy for a single silicon nanowire size (d=150 nm). (c) variation in spectral positions of band A and (d) band B for several nanowire sizes as a function of excitation energy. Black arrows denotes location of peak 1.